

PJQ5478

100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

60A

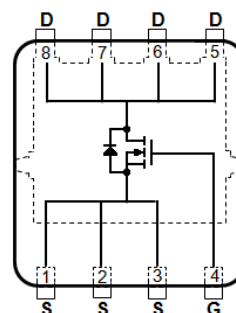
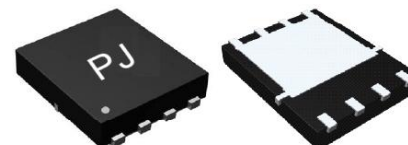
Features

- RDS(ON) , VGS@10V, ID@30A<12mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std.
(Halogen Free)

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams
- Marking: Q5478

DFN5060-8L



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _C =25°C	I _D	60	A
	T _C =100°C		38	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	150	
Power Dissipation	T _C =25°C	P _D	83	W
	T _C =100°C		33	
Continuous Drain Current	T _A =25°C	I _D	9	A
	T _A =70°C		7.5	A
Power Dissipation	T _A =25°C	P _D	2.0	W
	T _A =70°C		1.3	
Single Pulse Avalanche Energy (Note 6)		E _{AS}	156	mJ
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55~150	°C
Typical Thermal Resistance (Note 4,5)	Junction to Case	R _{θJC}	1.5	°C/W
	Junction to Ambient	R _{θJA}	62.5	

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =30A	-	9	12	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =+20V, V _{DS} =0V	-	-	±100	nA
Dynamic ^(Note 7)						
Total Gate Charge	Q _g	V _{DS} =50V, I _D =30A, V _{GS} =10V ^(Note 1,2)	-	145	-	nC
Gate-Source Charge	Q _{gs}		-	25	-	
Gate-Drain Charge	Q _{gd}		-	43	-	
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=1.0MHZ	-	3921	-	pF
Output Capacitance	C _{oss}		-	255	-	
Reverse Transfer Capacitance	C _{rss}		-	96	-	
Turn-On Delay Time	td _(on)	V _{DD} =50V, I _D =30A, V _{GS} =10V, R _G =3Ω ^(Note 1,2)	-	27	-	ns
Turn-On Rise Time	t _r		-	13	-	
Turn-Off Delay Time	td _(off)		-	15	-	
Turn-Off Fall Time	t _f		-	43	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	60	A
Diode Forward Voltage	V _{SD}	I _S =30A, V _{GS} =0V	-	0.8	1.3	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature T_J (MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^{\circ}\text{C}$.
4. The maximum current rating is package limited.
5. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. The test condition is $L=0.5\text{mH}$, $I_{AS}=25A$, $V_{DD}=25V$, $V_{GS}=10V$
7. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

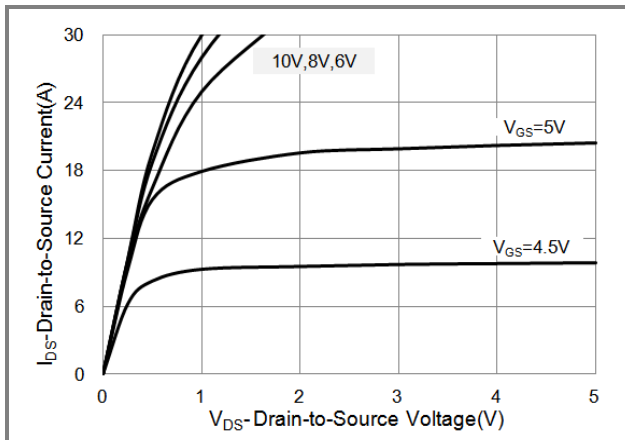


Fig.1 Output Characteristics

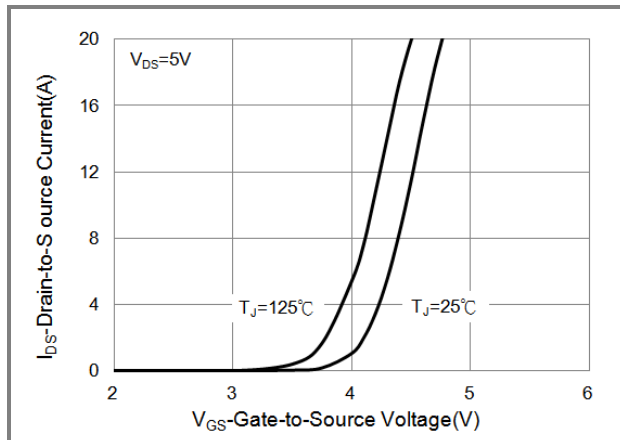


Fig.2 Transfer Characteristics

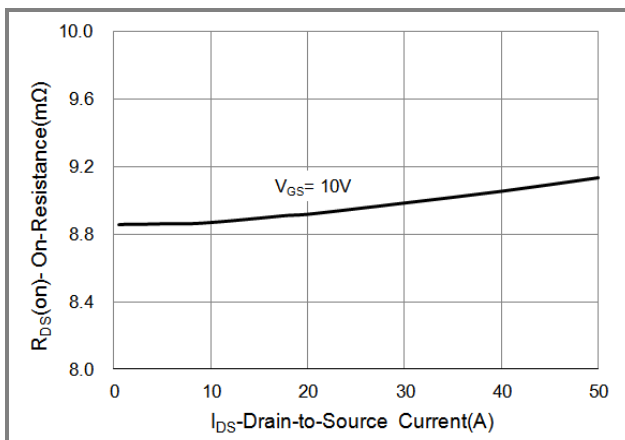


Fig.3 On-Resistance vs. Drain Current

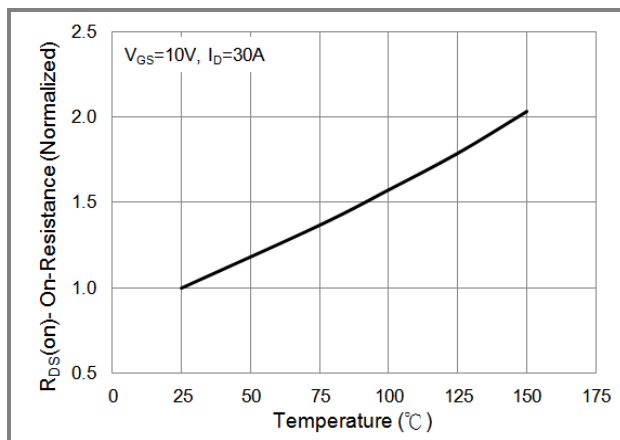


Fig.4 On-Resistance vs. Junction temperature

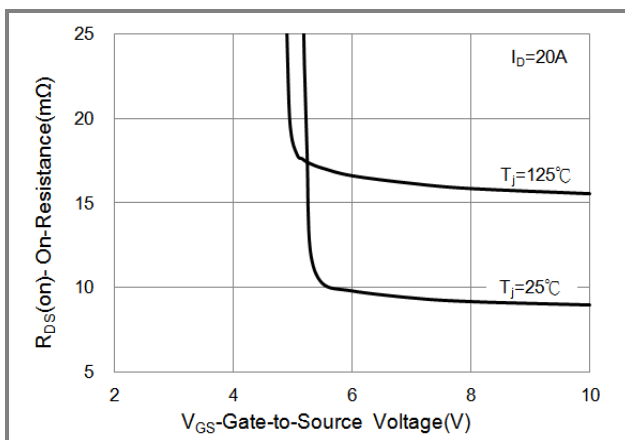


Fig.5 On-Resistance Variation with VGS.

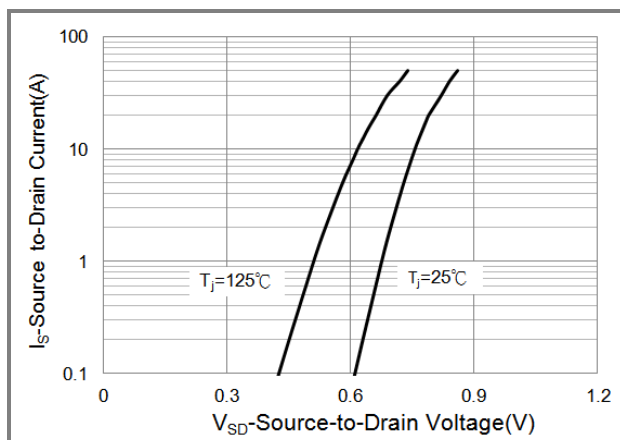


Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

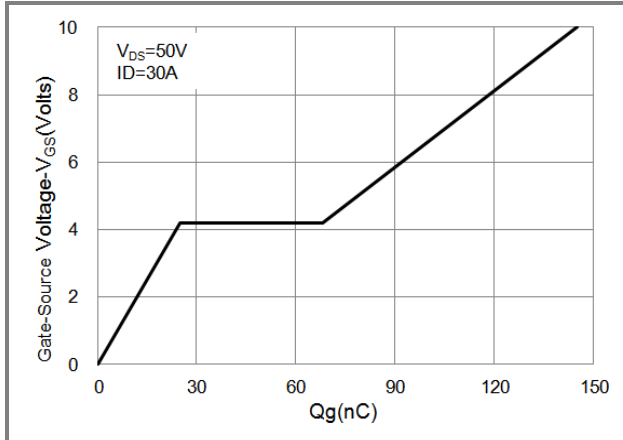


Fig.7 Gate-Charge Characteristics

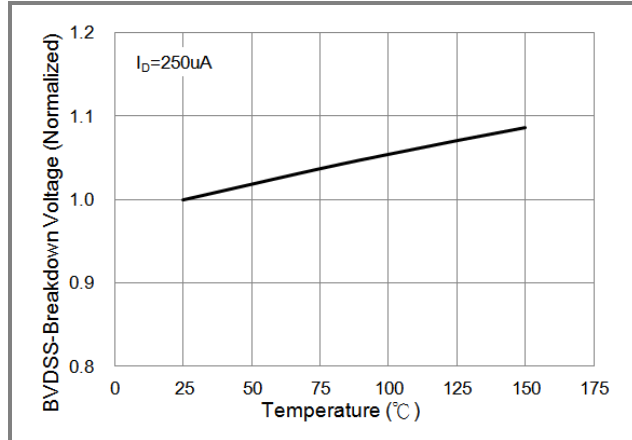


Fig.8 Breakdown Voltage Variation vs. Temperature

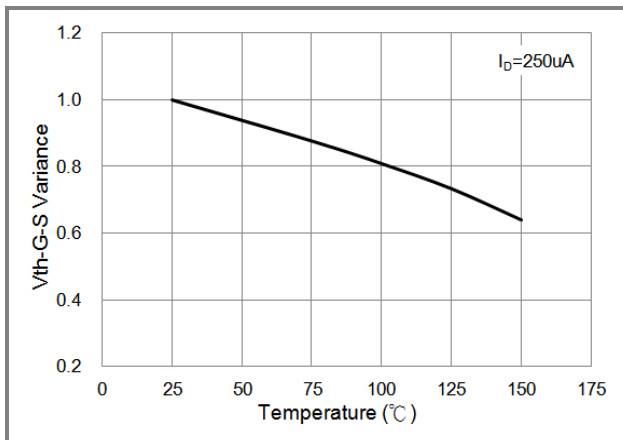


Fig.9 Threshold Voltage Variation with Temperature

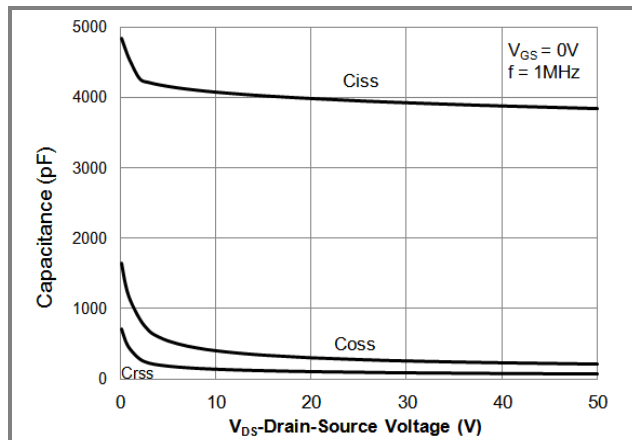


Fig.10 Capacitance vs. Drain-Source Voltage

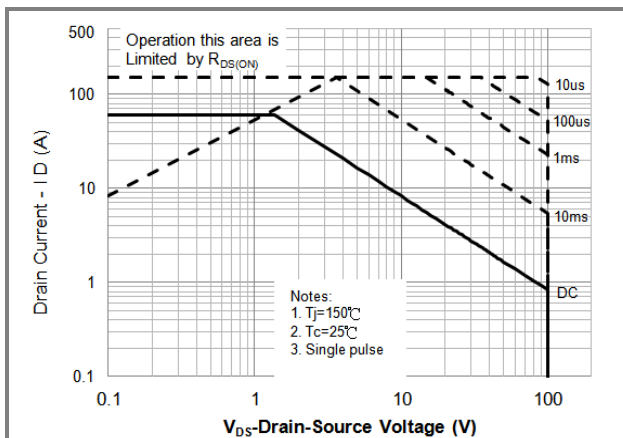


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

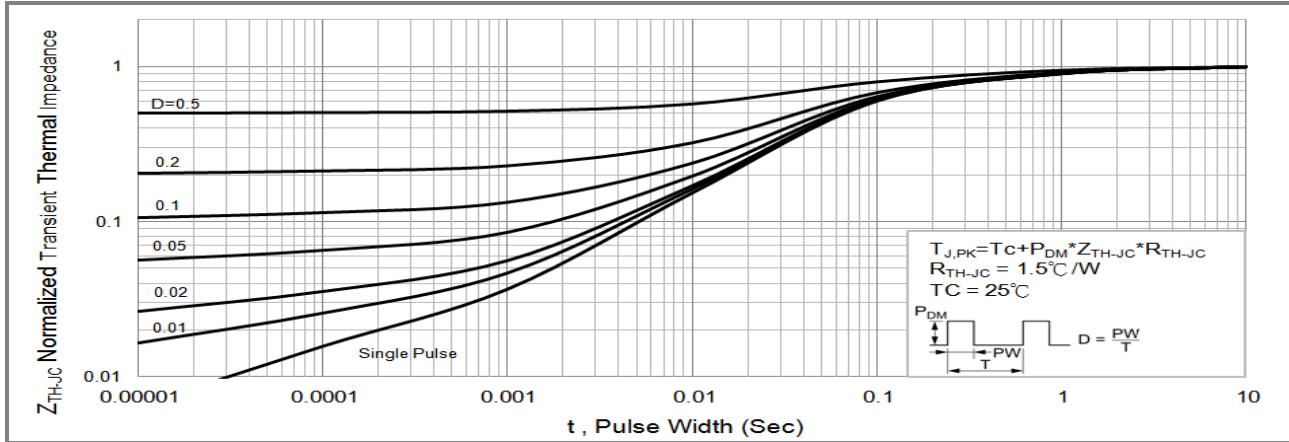


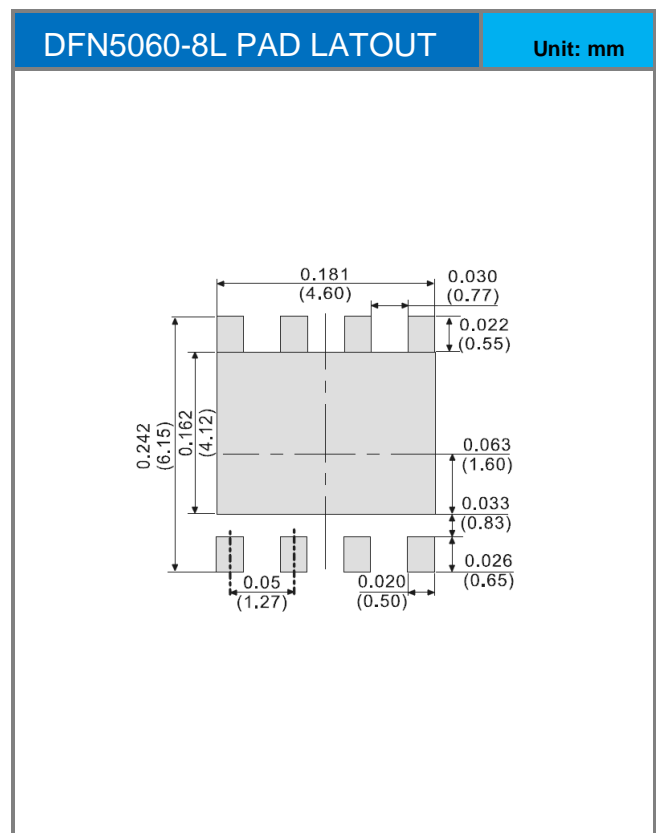
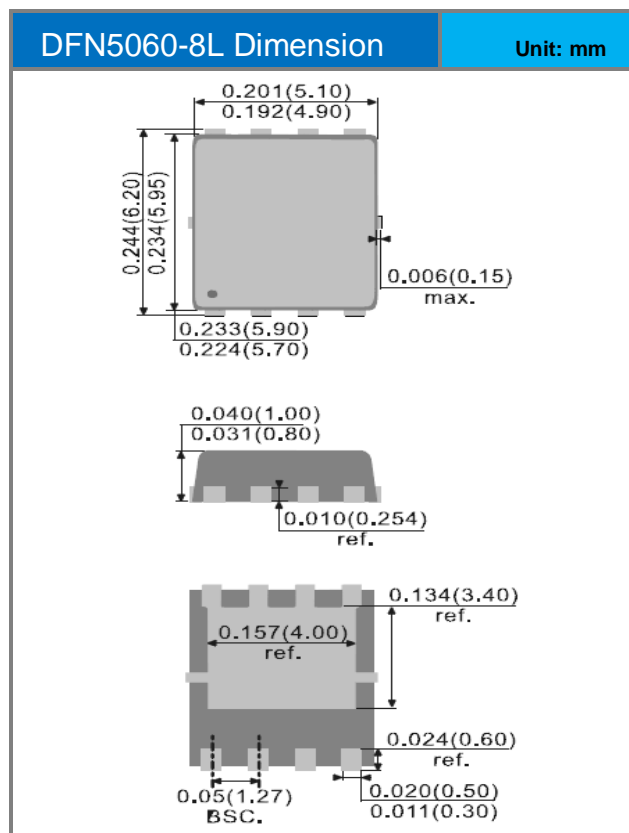
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

PJQ5478

PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJQ5478_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5478	Halogen free

Packaging Information & Mounting Pad Layout





PJQ5478

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